

235A 30V N-channel Enhancement Mode Power MOSFET

1 Description

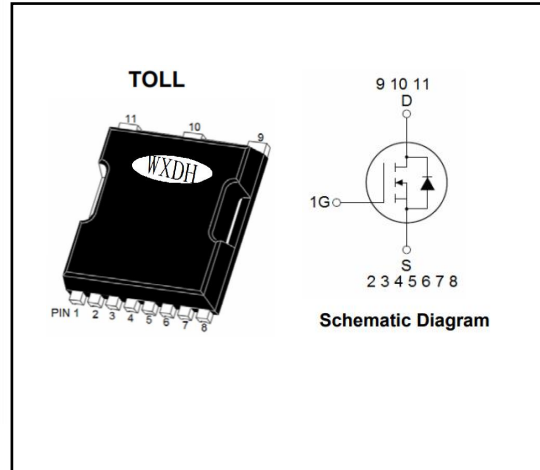
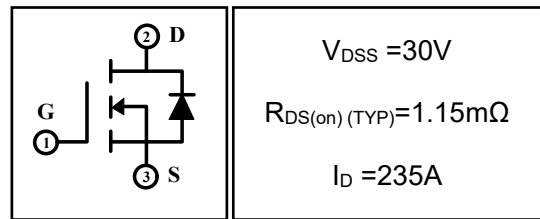
This N-channel enhancement mode power mosfets used advanced trench technology design, provided excellent $R_{DS(on)}$ and low gate charge. Which accords with the RoHS standard.

2 Features

- Low on resistance
- Low gate charge
- Fast switching
- Low reverse transfer capacitances
- 100% single pulse avalanche energy test
- 100% ΔV_{DS} test

3 Applications

- Power switching applications
- Power management for inverter systems
- Battery management



4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25°C, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-to-Source Voltage	V_{DSS}	30	V
Gate-to-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current	I_D	$T_C = 25^\circ C$	235
		$T_C = 100^\circ C$	148
Pulsed Drain Current ⁽¹⁾	I_{DM}	940	A
Single Pulse Avalanche Energy ⁽⁴⁾	E_{AS}	1400	mJ
Avalanche Current ⁽⁴⁾	I_{AS}	75	A
Power Dissipation	P_{tot}	$T_a = 25^\circ C$	2
		$T_C = 25^\circ C$	121
Junction Temperature Range	T_j	-55 ~ 150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 ~ 150	$^\circ C$

4.2 Thermal Characteristics

Parameter	Symbol	Value			Units
		Min	Typ	Max	
Thermal Resistance, Junction to Case-sink	R_{thJC}	--	--	1.03	$^\circ C/W$
Thermal Resistance, Junction to Ambient	R_{thJA}	--	--	62	$^\circ C/W$

4.3 Electrical Characteristics (T_c=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Units
			Min	Typ	Max	
Off Characteristics						
Drain-to-Source Breakdown Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V, T _C =25°C	30	---	---	V
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V, T _C =25°C	---	---	1	μA
		V _{DS} =30V, V _{GS} =0V, T _C =125°C	---	---	100	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2	V
Drain-to-Source on-state Resistance	R _{DS(on)}	V _{GS} =10V, I _D =160A	---	1.15	1.32	mΩ
		V _{GS} =4.5V, I _D =80A	---	1.7	2.1	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =15V, f=1.0MHz	---	8600	---	pF
Output Capacitance	C _{oss}		---	1142	---	
Reverse Transfer Capacitance	C _{rss}		---	728	---	
Gate Resisistance	R _G	V _{DD} =0V, V _{GS} =0V, F=1MHz	---	2.6	---	Ω
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	I _D =75A, V _{DD} =15V, V _{GS} =10V, R _{GEN} =10Ω	---	30	---	nS
Turn-on Rise Time	t _r		---	250	---	
Turn-off Delay Time	t _{d(off)}		---	331	---	
Turn-off Fall Time	t _f		---	240	---	
Total Gate Charge	Q _g	I _D =75A, V _{DD} =15V, V _{GS} =10V	---	193	---	nC
Gate-to-Source Charge	Q _{gs}		---	32	---	
Gate-to-Drain("Miller") Charge	Q _{gd}		---	46	---	
Drain-Source Diode Characteristics						
Diode Forward Voltage ⁽³⁾	V _{SD}	V _{GS} =0V, I _S =50A	---	---	1.3	V
Diode Forward Current	I _S		---	---	235	A
Reverse Recovery Time ⁽³⁾	t _{rr}	T _J =25°C, I _F =30A, dI _F /dt=100A/μS, V _{GS} =0V	---	80	---	nS
Reverse Recovery Charge ⁽³⁾	Q _{rr}		---	72	---	nC

Notes:

- 1: Repetitive rating, pulse width limited by maximum junction temperature.
- 2: Surface mounted on FR4 Board, t_s≤10sec.
- 3: Pulse width ≤ 300μs, duty cycle ≤ 2%.
- 4: L=0.5mH, I_D=75A, V_{ds}=24V, R=25Ω, V_{GATE}=30V, Start T_J=25°C.

5 Typical characteristics diagrams

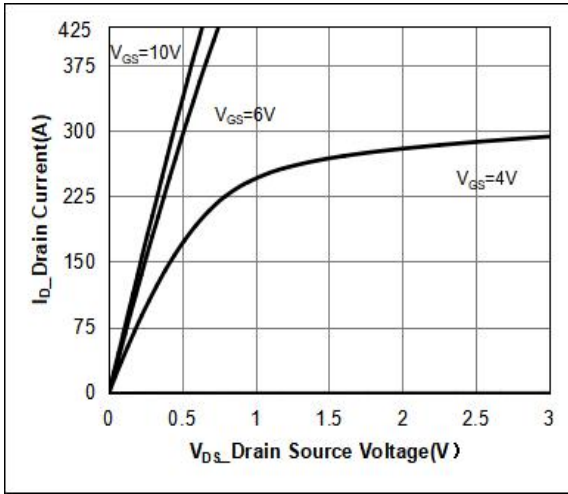


Figure 1 Output Characteristics

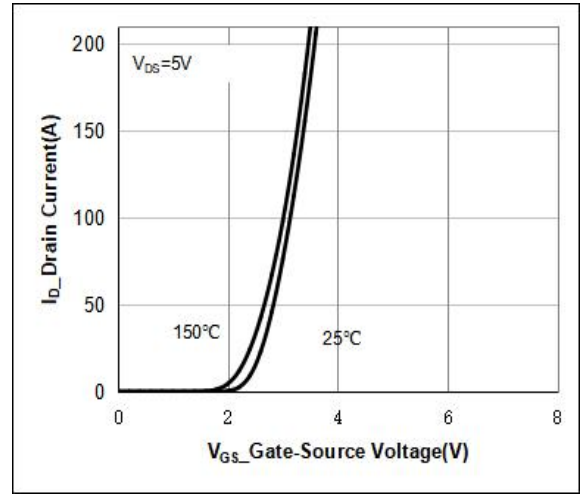


Figure 2 Transfer Characteristics

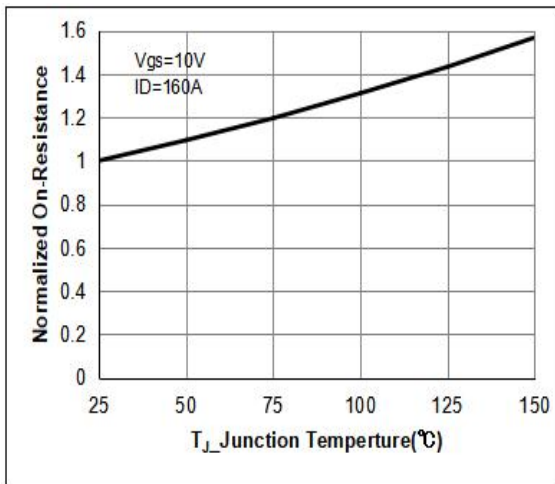


Figure 3. Rdson vs Temperature

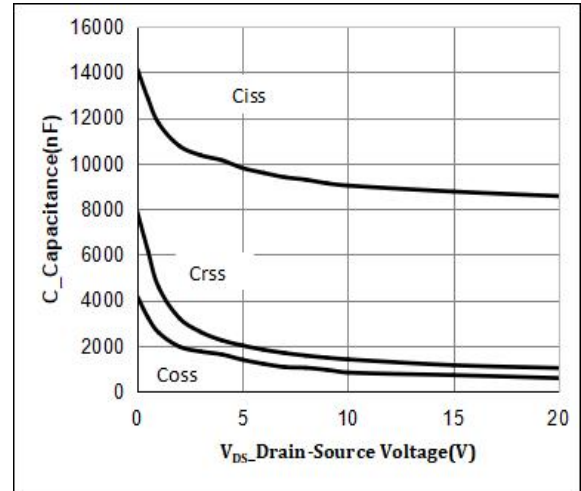


Figure 4. Capacitance Characteristics

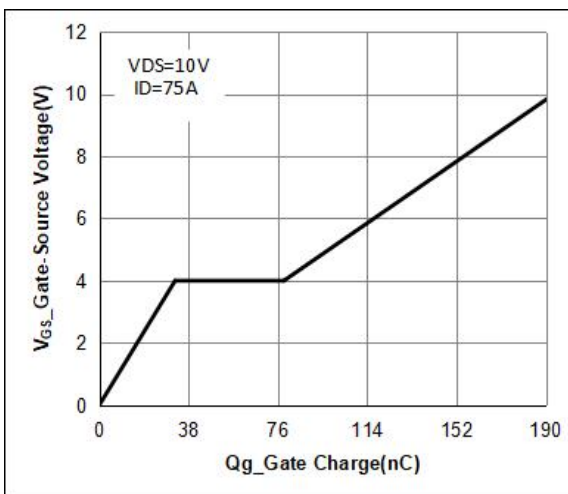


Fig 5. Gate Charge

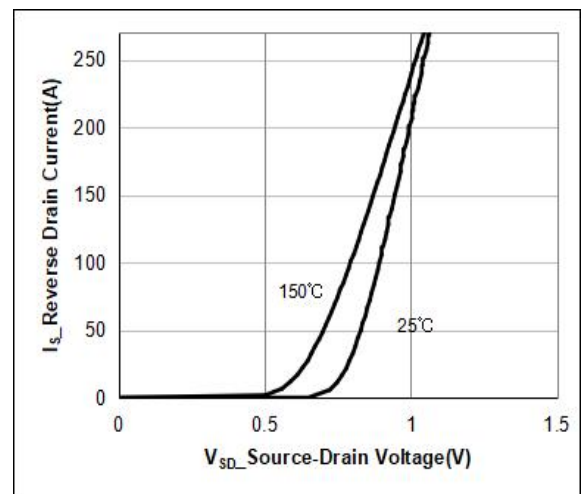


Fig 6. Source-Drain Diode Forward

5 Typical characteristics diagrams(continues)

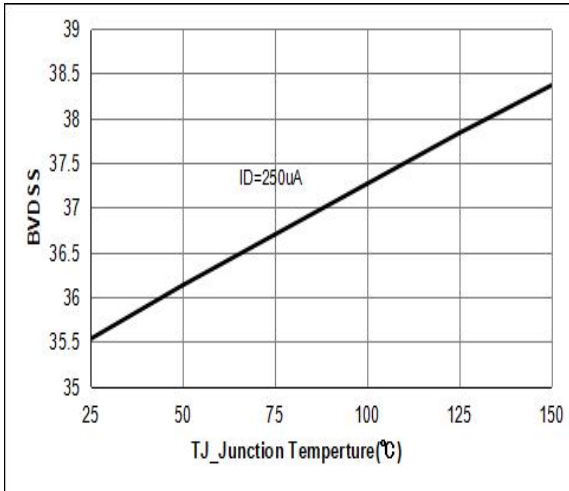


Figure7.BVDSS vs Junction Temperature

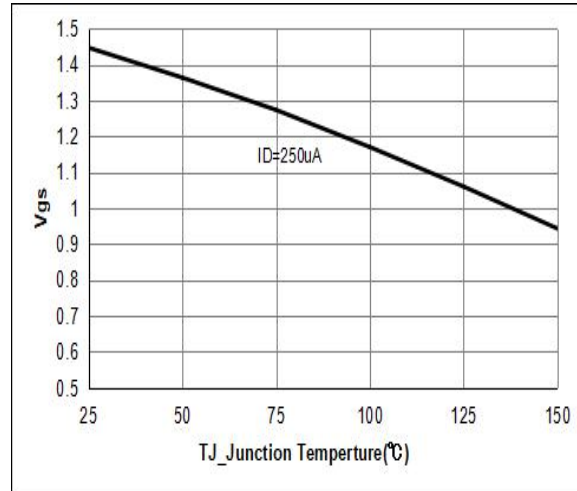


Figure8.VGS(th) vs Junction Temperature

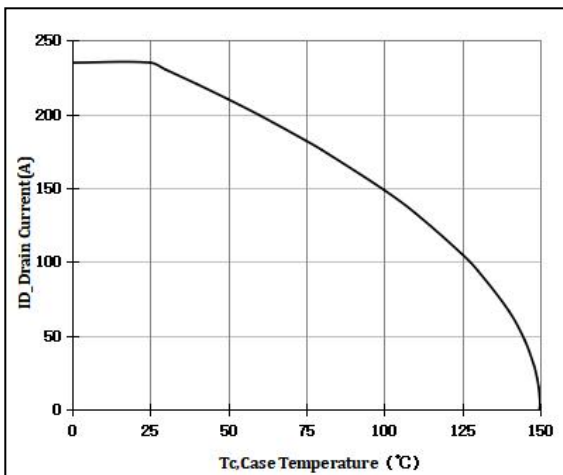


Figure 9. ID Current De-rating

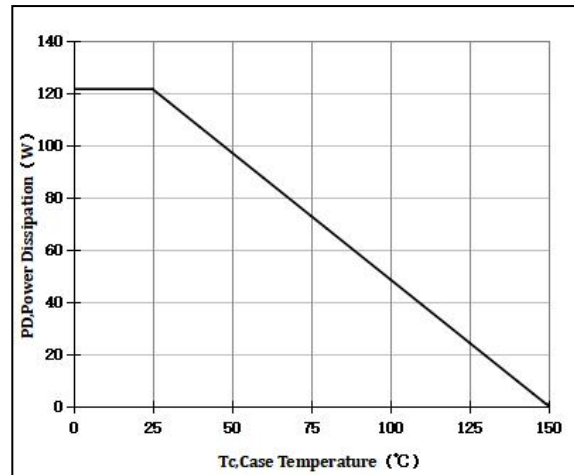


Figure 10. Power De-rating

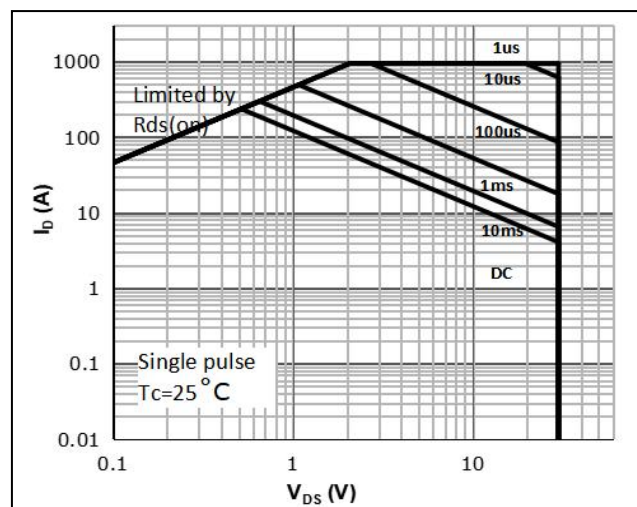


Figure 11. Safe Operating Area

5 Typical characteristics diagrams(continues)

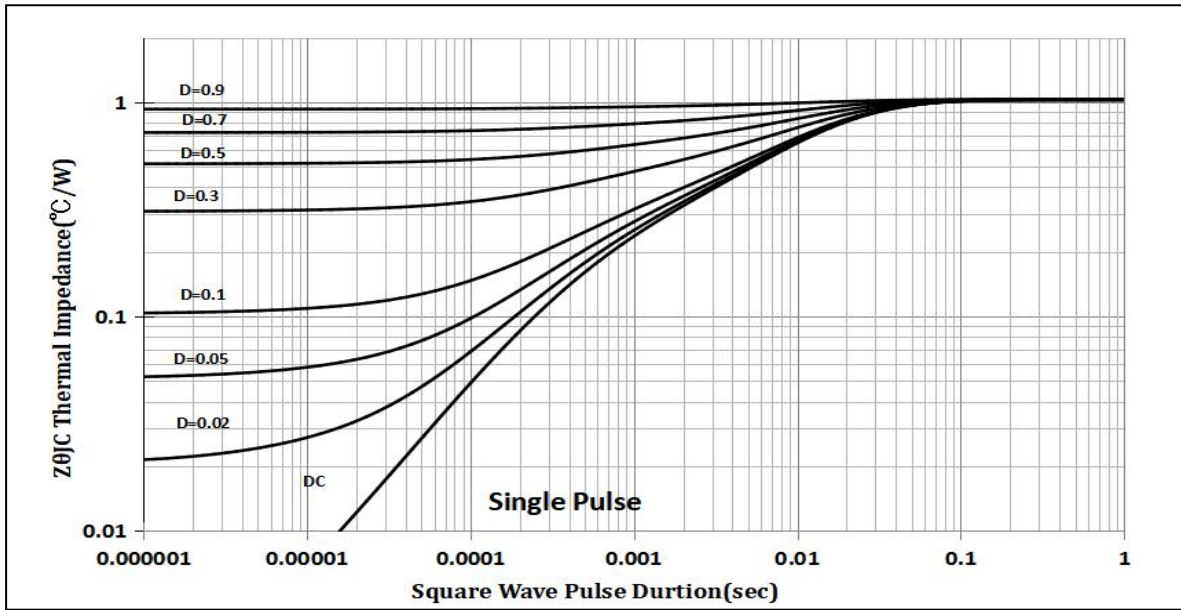
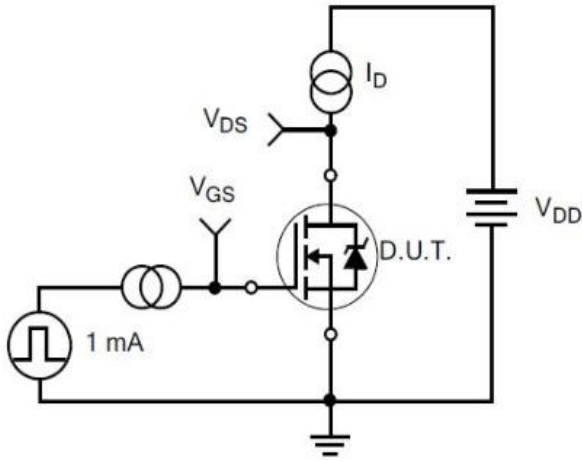
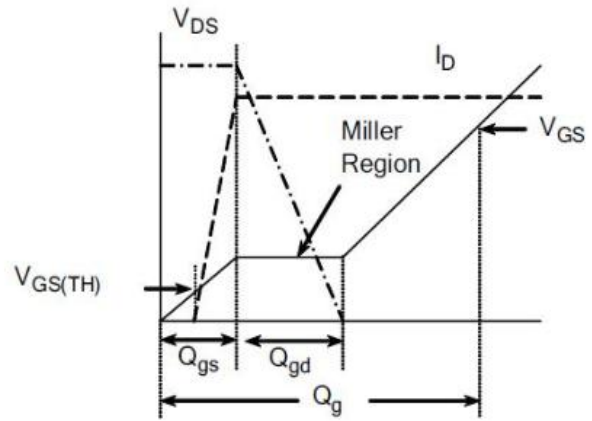


Fig 11. Normalized Maximum Transient Thermal Impedance

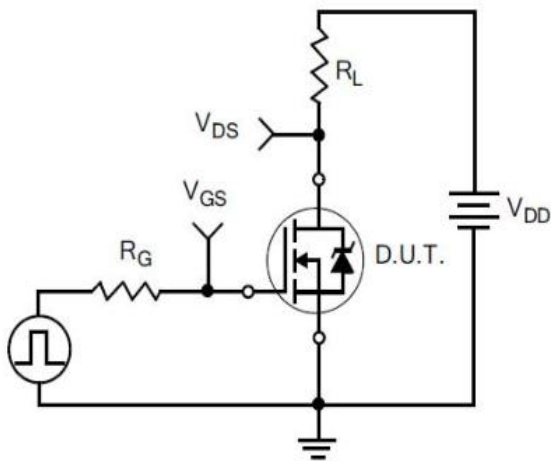
6 Typical Test Circuit and Waveform



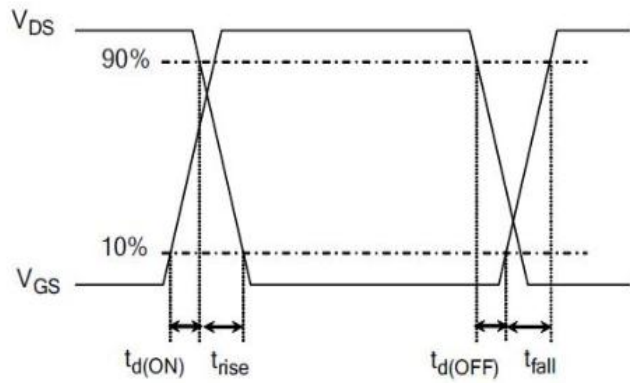
1) Gate Charge Test Circuit



2) . Gate Charge Waveform

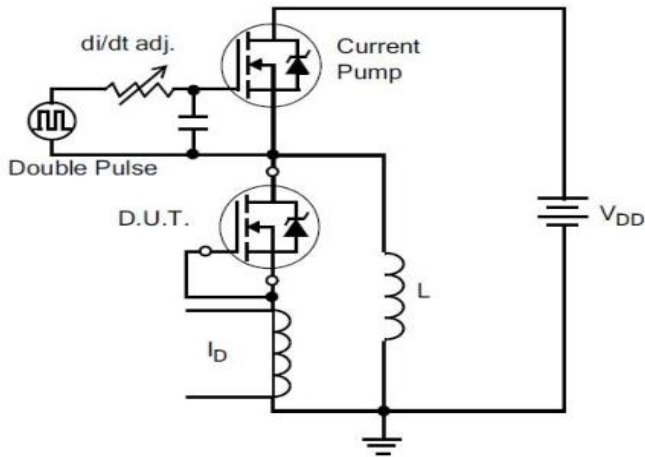


3) Resistive Switching Test Circuit

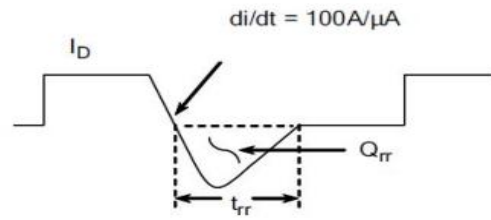


4) Resistive Switching Waveforms

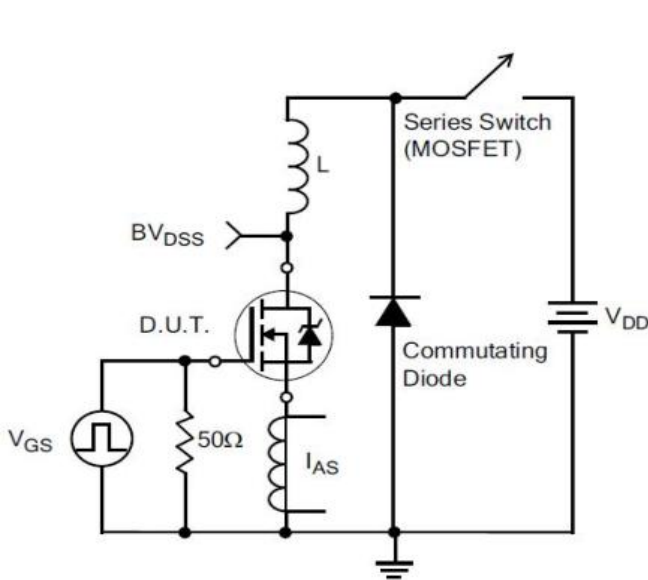
6 Typical Test Circuit and Waveform(continues)



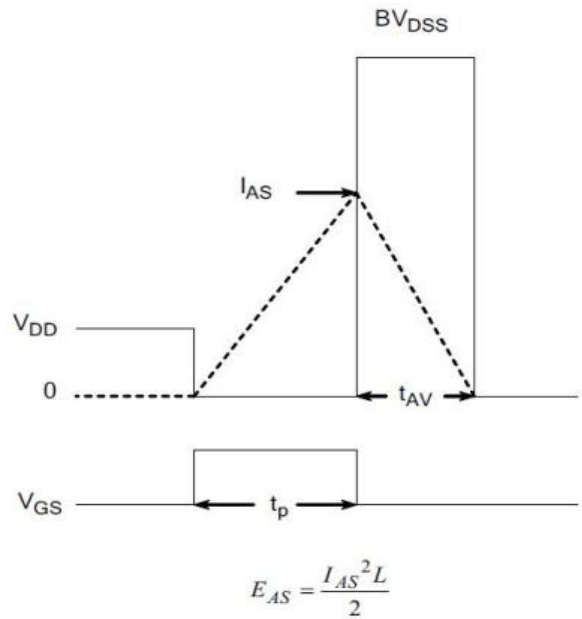
5) Diode Reverse Recovery Test Circuit



6) Diode Reverse Recovery Waveform

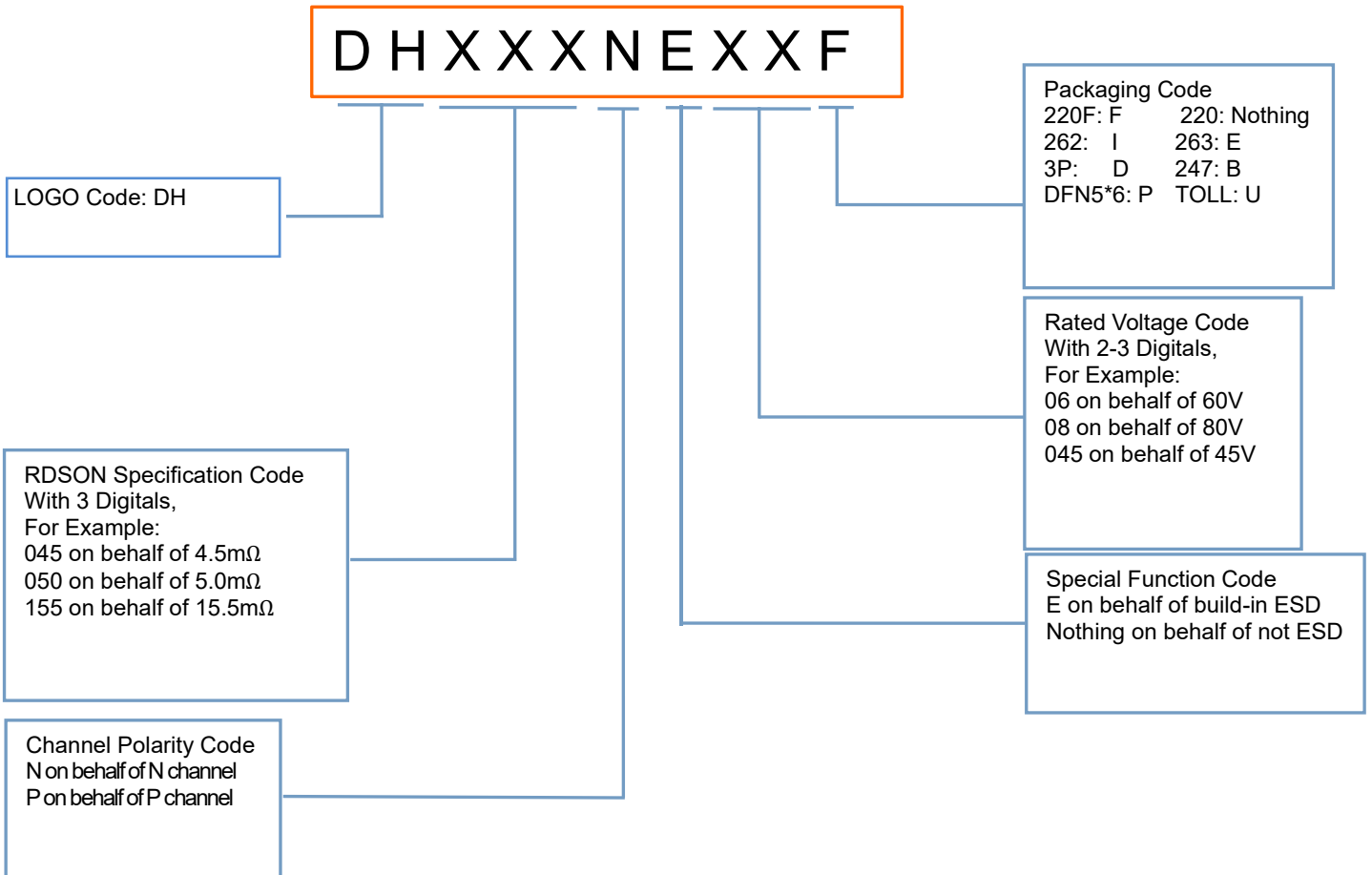


7) . Unclamped Inductive Switching Test Circuit



8) Unclamped Inductive Switching Waveforms

7 Product Names Rules

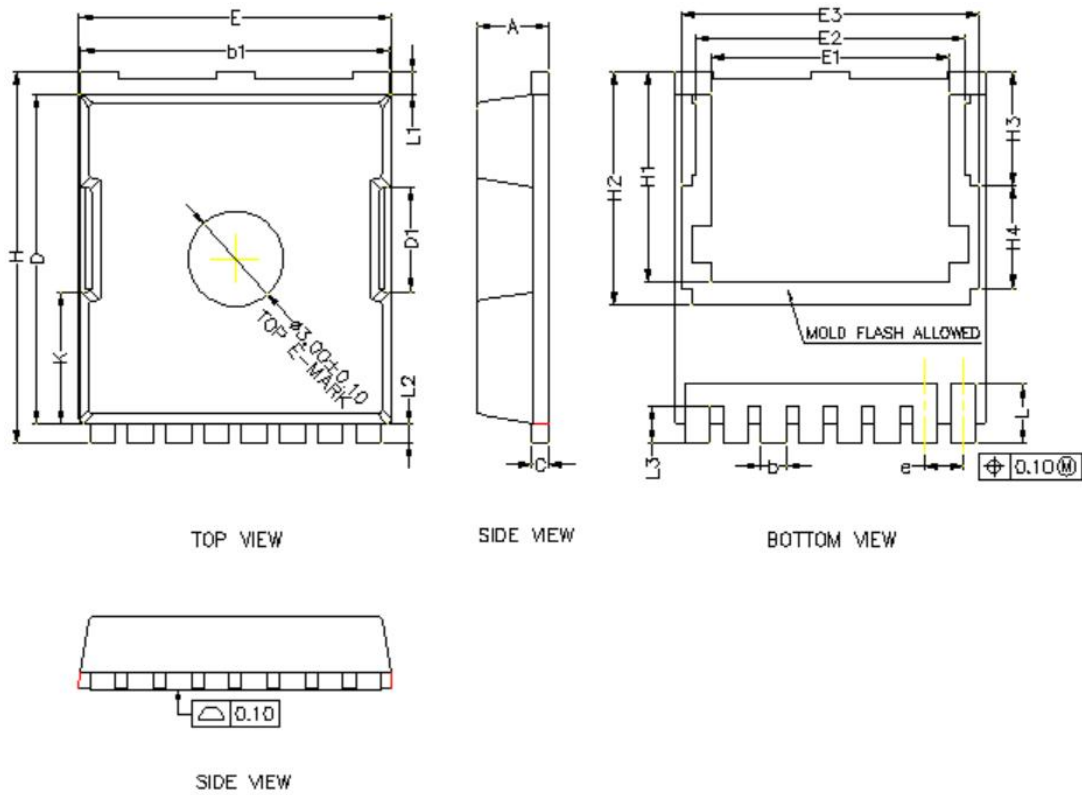


8 Product Specifications and Packaging Models

Product Model	Package Type	Mark Name	RoHS	Package	Quantity
DH012N03U	TOLL	DH012N03U	Pb-free	Tape & Reel	1800/box

9 Dimensions

TOLL:



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
b	0.70	0.80	0.90
b1	9.70	9.80	9.90
c	0.40	0.50	0.60
D	10.28	10.43	10.58
D1	3.15	3.30	3.45
E	9.70	9.90	10.10
E1	7.35	7.50	7.65
E2	8.35	8.50	8.65
E3	9.31	9.46	9.61
e	1.10	1.20	1.30
H	11.48	11.73	11.88
H1	6.55	6.65	6.75
H2	7.20	7.35	7.50
H3	3.44	3.59	3.74
H4	3.11	3.26	3.41
K	4.03	4.18	4.33
L	1.60	1.85	2.10
L1	0.55	0.70	0.85
L2	0.45	0.60	0.75
L3	1.00	1.15	1.30

10 Attentions

- Jiangsu Donghai Semiconductor Technology CO.,LTD. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of Donghai products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

11 Appendix

Revision history:

Date	REV.	Description	Page
2021.11.25	1.0	Original	10
2022.08.22	2.0	Original	10